



SURFACE MOUNT HIGH EFFICIENCY RECTIFIER US1AB ~ US1MB

Surface Mount High Efficiency Rectifier

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Built-in strain relief, ideal for automated placement
- Fast switching speed for high efficiency
- Glass passivated chip junction
- High temperature soldering guaranteed:
260°C/10 seconds
- RoHS and REACH Compliance



DO-214AA (SMB)



RoHS
COMPLIANT

Mechanical Data

Case:	JEDEC DO-214AA molded plastic over glass passivated chip
Polarity:	Color band denotes cathode end.
Terminal:	Solder plated, solderable per MIL-STD 750, Method 2026
Mounting Position:	/
Weight:	0.003 ounce, 0.093 gram

Maximum Ratings ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	US1AB	US1BB	US1DB	US1GB	US1JB	US1KB	US1MB	Unit	Conditions
VRRM	Max Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V	
VRMS	Max RMS Voltage	35	70	140	280	420	560	700	V	
VDC	Max DC Blocking Voltage	50	100	200	400	600	800	1000	V	
I(AV)	Max Average Forward Rectified Current	1.0							A	$T_A=55^{\circ}\text{C}$
IFSM	Peak Forward Surge Current, 8.3ms single half sine	30							A	JEDEC method
TJ,TSTG	Operating and Storage Temperature Range	-55 to +150							$^{\circ}\text{C}$	

Electrical Characteristics ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	US1AB	US1BB	US1DB	US1GB	US1JB	US1KB	US1MB	Unit	Conditions
VF	Max Instantaneous Forward Voltage	1.0		1.3			1.7		V	1.0A
Rθ-JA	Typical Thermal Resistance	88							°C/W	Note 2
Rθ-JL		28								
IR	Max DC Reverse Current at Rated DC Blocking Voltage	5							μA	TA=25°C
		100								TA=125°C
TRR	Maximum reverse recovery time	50				75			nS	Note 1
CJ	Typical Junction capacitance	20				15			pF	Measured at 1.0MHz/4.0V

Note:

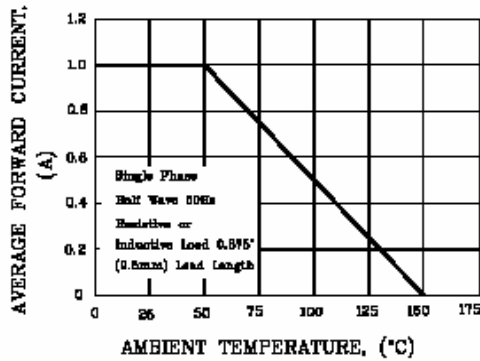
1. Test conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$
2. Thermal resistance from junction to ambient and from junction to lead mounted on PCB with 0.2"x0.2" (5.0x5.0mm) copper pad areas.

Rev. 0 2010-07-15

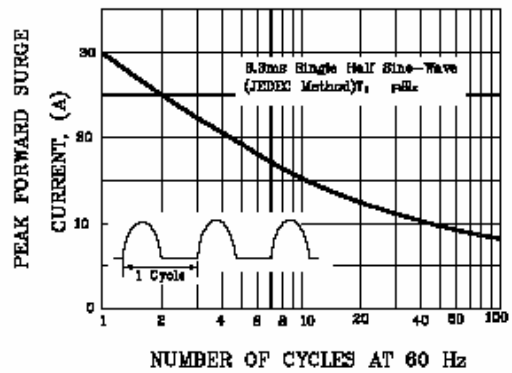
US1AB ~ US1MB

RATINGS AND CHARACTERISTIC CURVES US1A THRU US1M

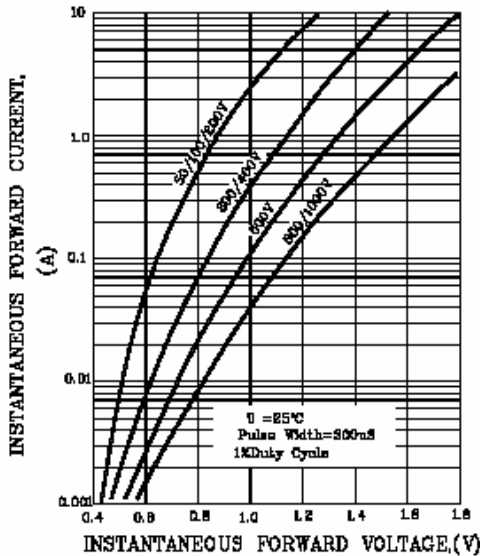
**FIG.1-TYPICAL FORWARD CURRENT
DERATING CURVE**



**FIG.2-MAXIMUM NON-REPETITIVE PEAK
FORWARD SURGE CURRENT**



**FIG.3-TYPICAL INSTANTANEOUS
FORWARD CHARACTERISTICS**



**FIG.4-TYPICAL REVERSE
CHARACTERISTICS**

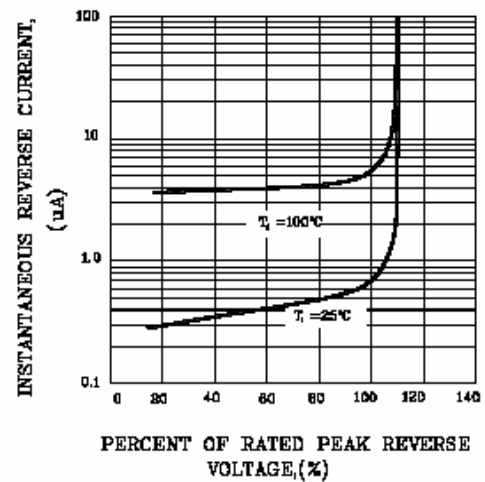
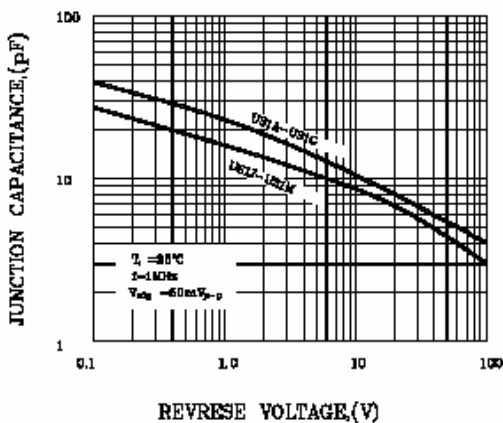
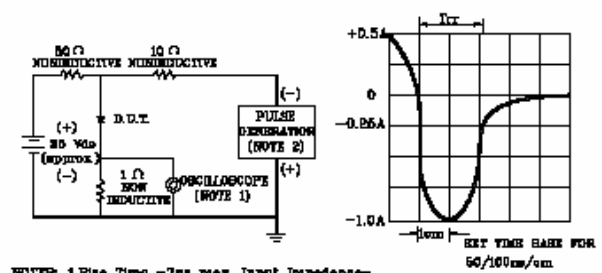


FIG.5-TYPICAL JUNCTION CAPACITANCE

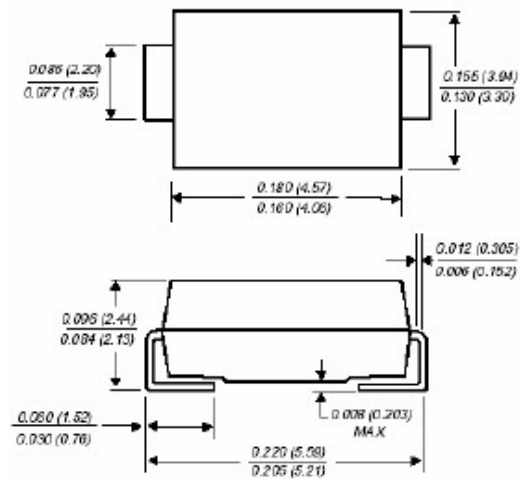


**FIG.6-TEST CIRCUIT DIAGRAM AND
REVERSE RECOVERY TIME CHARACTERISTIC**



NOTES: 1. Rise Time - T_{rs} max. Input Impedance - 1 megohm. 25pF

2. Rise time - 10ns MAX. Source Impedance - 50 ohms

US1AB ~ US1MB**Dimensions in inches (mm)***Dimensions in inches and (millimeters)***DO-214AA (SMB)****Contact us:****US HEADQUARTERS****MEI SEMI INC.****2902** Corvin Drive, Santa Clara, CA95051, USA

Tel: 1-408-733-0808 Fax: 1-408-733-2828